

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1.-4. (Canceled)

5. (Previously Presented) A method of manufacturing a ferroelectric layer, comprising:

forming a first ferroelectric section in which crystal defects are intentionally created, by using a first material used for forming a ferroelectric in which part of substances in a stoichiometric composition is absent; and

forming, over the first ferroelectric section, a second ferroelectric section which has less crystal defects than the first ferroelectric section, by using a second material used for forming a ferroelectric which is closer to the stoichiometric composition compared to the ferroelectric which is formed by using the first material..

6. (Previously Presented) The method of manufacturing a ferroelectric layer as defined in claim 5, further comprising:

forming a third ferroelectric section including space charges generated by causing a crystal defect to occur over the second ferroelectric section,

the polarities of the space charges in the first ferroelectric section and the third ferroelectric section being different from each other.

7.-10. (Canceled)

11. (Previously Presented) A method of manufacturing a ferroelectric layer, comprising:

forming a first ferroelectric section in which crystal defects are intentionally created, by performing crystallization heat treatment for first oxygen partial pressure, and

forming a second ferroelectric section which has less crystal defects than the

first ferroelectric section, by performing crystallization heat treatment for second oxygen partial pressure which is greater than the first oxygen partial pressure.

12.-18. (Canceled)

19. (Previously Presented) The method of manufacturing a ferroelectric layer as defined in claim 5, wherein the first and second ferroelectric sections are formed by a vapor phase method.

20. (Previously Presented) The method of manufacturing a ferroelectric layer as defined in claim 11, wherein the first oxygen partial pressure is set at 0.02 MPa or less.

21. (Canceled)

22. (Previously Presented) The method of manufacturing a ferroelectric layer as defined in claim 5, wherein the crystal defects formed in the first ferroelectric section cause a positive or negative effective charge to be generated in a ferroelectric.